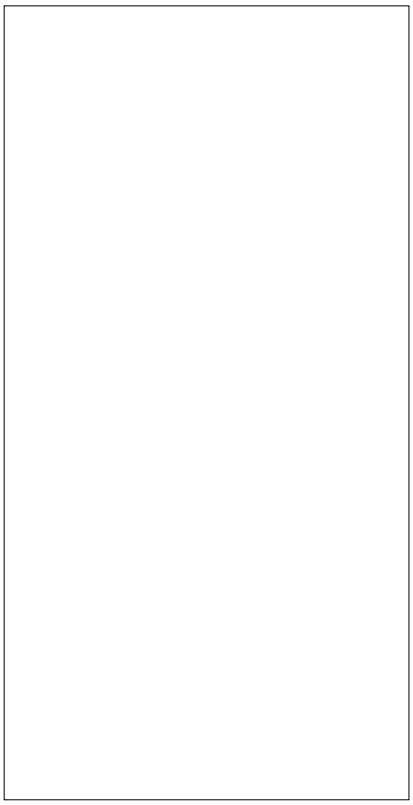
JCT640AH 40A SCR

Rev A.1.1

DESCRIPTION:

With high ability to withstand the shock loading of large current, JCT640AH SCR provides high dV/dt rate with strong resistance to electromagnetic interference.It is especially recommended for use on solid state relay, motorcycle, power charger, T-tools etc. From all three terminals to external heatsink,JCT640AH provides a rated insulation voltage of 2500 $V_{RMS,}$ complying with UL standards (File ref: E252906). Package TO-220A is RoHS compliant.



MAIN FEATURES

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol

Peak gate current (t_p=20μs , T_j=150)	I_{GM}	10	A
Average gate power dissipation (T_j=150)	$P_{G(AV)}$	1	W
Peak gate power	P_{GM}	20	W
Peak pulse voltage (T_j=25 ; non-repetitive,off-state;FIG.7)	V_{pp}	0.5	kV

ELECTRICAL CHARACTERISTICS (T_j=25 unless otherwise specified)

Symbol	Test Condition	Value			Unit
		MIN.	TYP.	MAX.	
I_{GT}	V_D=12V R_L=33Ω	-	-	35	mA
V_{GT}		-	-	1	V
V_{GD}	V_D=V_{DRM} T_j=150 R_L=3.3kΩ	0.2	-	-	V
I_L	I_G=1.2I_{GT}	-	-	80	mA
I_H	I_T=500mA	-	-	70	mA
dV/dt	V_D=400V Gate Open T_j=125	1300	-	-	V/μs
	V_D=400V Gate Open T_j=150	700	-	-	
t_{on}	I_G=40mA I_A=400mA I_R=40mA T_j=25	-	2	-	μs
t_{off}		-	60	-	

STATIC CHARACTERISTICS

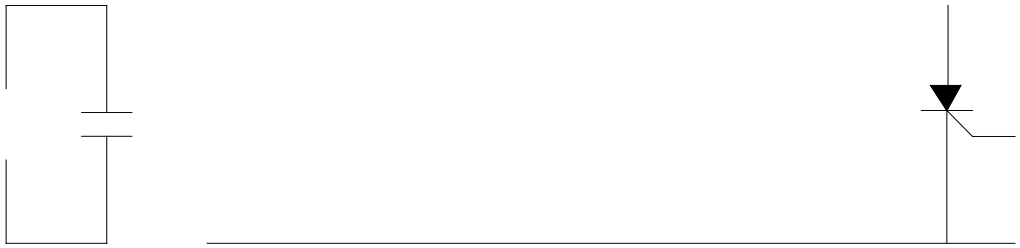
Symbol	Parameter		Value(MAX)	Unit
V_{TM}	I_{TM}=80A t_p=380μs	T_j=25	1.55	V
V_{TO}	Threshold voltage	T_j=150	0.65	V
R_D	Dynamic resistance	T_j=150	17	mΩ
I_{DRM}	V_D=V_{DRM} V_R=V_{RRM}	T_j=25	5	μA
I_{RRM}		T_j=150	8	mA

ORDERING INFORMATION

J CT 6 40 A H

- J: JieJie Microelectronics Co., Ltd.
- CT: SCRs
- 6: V_{DRM} /V_{RRM} 600V

FIG.7 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards.

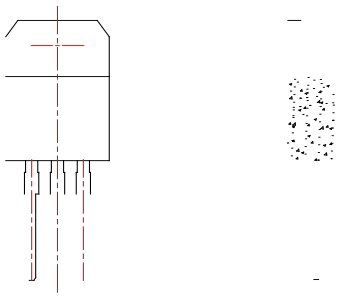


ORDERING INFORMATION

Order code	Voltage V_{DRM}/V_{RRM} (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JCT640AH	600	35	TO-220A(Ins)	50	Tube

Document

PACKAGE MECHANICAL DATA



JCT640AH